Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt[®]



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DESIGN SUPPORT TOOLS [click logo to get started.



PRIMARY CHARACTERISTICS					
I _{F(AV)}	1 A				
V _R	200 V				
V _F at I _F (typ. 125 °C)	0.74 V				
t _{rr}	25 ns				
T _J max.	175 °C				
Package	SMF (DO-219AB)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		200	V			
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$	1	А			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	35	A			
Operating junction and storage temperature range	T _J , T _{Stg}		-65 to +175	°C			

Note

⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	IBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-	
Forward voltage V _F		$I_F = 1 A$	-	0.87	0.93	V
		I _F = 1 A, T _J = 125 °C	-	0.74	0.8	
		$V_{R} = V_{R}$ rated	-	-	2	
Reverse leakage current I _R		T _J = 125 °C, V _R = V _R rated	-	0.5	8	μΑ
Junction capacitance	C _T	V _R = 200 V	-	5	-	pF

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RoHS

COMPLIANT HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \ dI_F/dt = 50 \text{ A}$	õs, V _R = 30 V	-	24	-		
Reverse recovery time	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	ns	
		T _J = 125 °C		-	23	-		
Deck receiver aurrent		T _J = 25 °C	$I_F = 1 A$	-	1.6	-	^	
Peak recovery current	IRRM	T _J = 125 °C	dl _F /dt = 200 A/µs V _R = 160 V	-	2.5	-	A	
		T _J = 25 °C		-	13	-		
Reverse recovery charge Q _{rr}		T _J = 125 °C]	-	30	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	+175	°C	
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W	
Approvimate weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style SMF (DO-219AB)		М	DH		

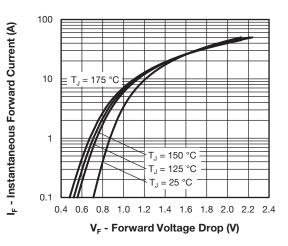


Fig. 1 - Typical Forward Voltage Drop Characteristics

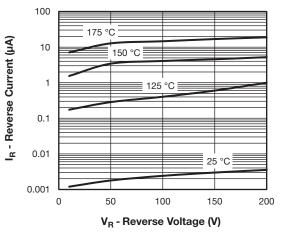
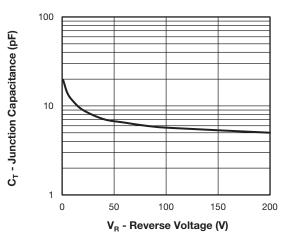


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

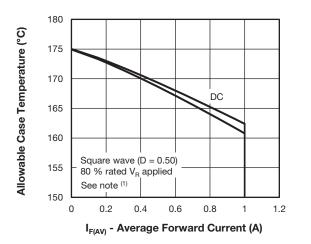


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

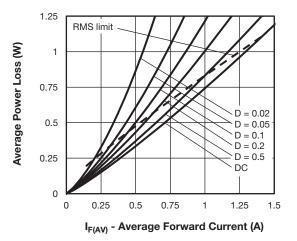


Fig. 5 - Forward Power Loss Characteristics

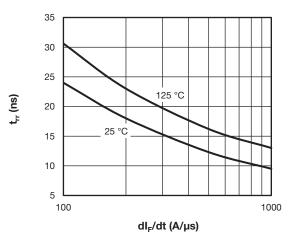


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

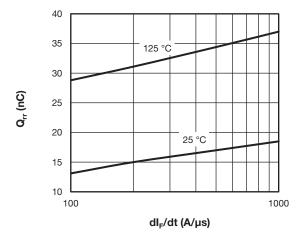


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (\mbox{I}_{F(AV)}/D) \mbox{ (see fig. 5);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 - D); I}_{R} \mbox{ at } \mbox{V}_{R1} = \mbox{rated } \mbox{V}_{R} \end{array}$

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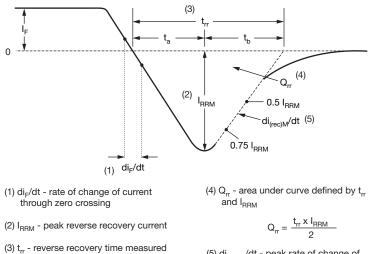
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VS-1EFH02HM3

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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current. (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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	VS-	1	Е	F	н	02	н	М3
L	1	2	3	4	5	6	7	8
Γ	1 ·	- Visl	nay Sem	nicondu	ctors pr	oduct		
	2 -	- Cur	rent rati	ng (1 =	1 A)			
	3 -	- Circ	cuit cont	figuratio	n:			
		E =	single c	liode				
[4 -	F=	SMF pa	ackage				
Ē	5 -	- Pro	cess typ	be,				
		H =	hyperfa	ast recov	very			
	6	- Vol	tage coo	de (02 =	200 V)			
Γ	7 -	• H=	AEC-Q	101 qua	alified			
	8 -	- M3	= halog	en-free,	RoHS-	complia	ant, and	termina

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-1EFH02HM3/I	10 000	10 000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618				
Packaging information	www.vishay.com/doc?95577				
SPICE model	www.vishay.com/doc?96012				

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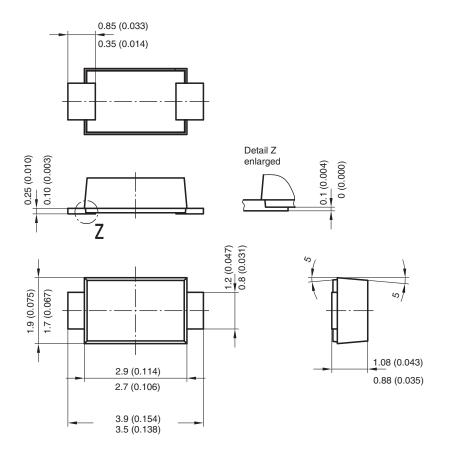
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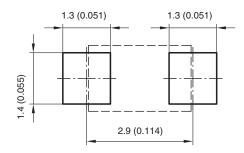
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SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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